

MS652S

MS652S Information

Contraction of the second seco	Part Number Manufacturer Category Description Package	MS652S Microsemi Corporation Discrete Semiconductor Products Transistors - Bipolar (BJT) - RF TRANS RF BIPO 25W 2A M123 M123 For the pricing/inventory/lead time, please contact	
For Reference Only		us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

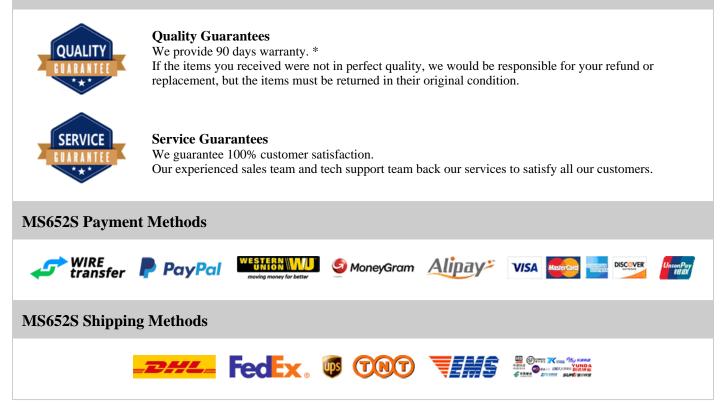
Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



MS652S Specifications

Manufacturer Part Number	MS652S	
Manufacturer	Microsemi Corporation	
Category	Discrete Semiconductor Products	
	Transistors - Bipolar (BJT) - RF	
Package	M123	
Series	-	
Transistor Type	NPN	
Voltage - Collector Emitter Breakdown (Max)	16V	
Frequency - Transition	450MHz ~ 512MHz	
Noise Figure (dB Typ @ f)	-	
Gain	10dB	
Power - Max	25W	
DC Current Gain (hFE) (Min) @ Ic, Vce	10 @ 200mA, 5V	
Current - Collector (Ic) (Max)	2A	
Operating Temperature	200°C (TJ)	
Mounting Type	Chassis Mount	
Package / Case	M123	
Supplier Device Package	M123	
	Report errors?	

MS652S Guarantees



If you have any question about MS652S, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com